

## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

### Listing of Claims:

1-10. (Canceled)

11. (Currently Amended) ~~The temperature sensor of claim 7,~~ A temperature sensor, comprising:

a comparator circuit having an output node and a variable current node, wherein the output node is a first voltage at a given temperature when a current at the variable current node is less than a threshold current, and a different second voltage at the given temperature when the current at the variable current node is more than the threshold current;

first and second variable resistance circuits connected in series between the variable current node of the comparator and a supply voltage, wherein the first variable resistance circuit includes m resistors connected in series, where n is an integer of 4 or more and the m resistors have different resistance values from each other, and wherein the second variable resistance circuit includes n resistors connected in series, where m is an integer of 4 or more and the n resistors have different resistance values from each other;

a first switching circuit which selectively bypasses individual ones of the m resistors of the first variable resistance circuit; and

a second switching circuit which selectively bypasses individual ones of the n resistors of the second variable resistance circuit,

wherein the first switching circuit comprises at least m transistors connected across respective ones of the m resistors, wherein gate terminals of the m transistors are responsive to a first input test signal to selectively bypass the m resistors,

respectively, and wherein the second switching circuit comprises at least  $n$  transistors connected across respective ones of the  $n$  resistors, wherein gate terminals of the  $n$  transistors are responsive to a second input test signal to selectively bypass the  $n$  resistors, respectively.

12. (Currently Amended) The temperature sensor of claim 11, wherein  $m$  equals  $n$ , and wherein resistance values of the  $m$  resistors of the first variable resistance circuit are respectively the same as resistance values of the  $n$  resistors of the second variable resistance circuit ~~8, wherein the first switching circuit comprises at least  $m$  transistors connected across respective ones of the  $m$  resistors, wherein gate terminals of the  $m$  transistors are responsive to a first input test signal to selectively bypass the  $m$  resistors, respectively, and wherein the second switching circuit comprises at least  $n$  transistors connected across respective ones of the  $n$  resistors, wherein gate terminals of the  $n$  transistors are responsive to a second input test signal to selectively bypass the  $n$  resistors, respectively.~~

13. (Currently Amended) The temperature sensor of claim 12, wherein one resistor among the  $n$  resistors has a lowest resistance value, and wherein the remaining resistors among the  $n$  resistors have resistance values which are multiples of the resistance value of the lowest resistance value ~~9, wherein the first switching circuit comprises at least  $m$  transistors connected across respective ones of the  $m$  resistors, wherein gate terminals of the  $m$  transistors are responsive to a first input test signal to selectively bypass the  $m$  resistors, respectively, and wherein the second switching circuit comprises at least  $n$  transistors connected across respective ones of the  $n$  resistors, wherein gate terminals of the  $n$  transistors are responsive to a second input test signal to selectively bypass the  $n$  resistors, respectively.~~

14. (Currently Amended) The temperature sensor of claim 12, wherein one resistor  $R_1$  among the  $n$  resistors has a lowest resistance value  $x$ , and wherein the remaining resistors  $R_2, R_3, \dots, R_{n-1}$  among the  $n$  resistors have resistance values of

~~$x \cdot 2, x \cdot 4, \dots, x \cdot (2n-1)$  10, wherein the first switching circuit comprises at least  $m$  transistors connected across respective ones of the  $m$  resistors, wherein gate terminals of the  $m$  transistors are responsive to a first input test signal to selectively bypass the  $m$  resistors, respectively, and wherein the second switching circuit comprises at least  $n$  transistors connected across respective ones of the  $n$  resistors, wherein gate terminals of the  $n$  transistors are responsive to a second input test signal to selectively bypass the  $n$  resistors, respectively.~~

15. (Original) The temperature sensor of claim 11, further comprising a trimming circuit connect in parallel to the first variable resistance circuit, wherein the trimming circuit includes a second set of  $m$  transistors connected across the  $m$  resistors of the first variable resistance circuit, respectively, and  $m$  latch circuits which selectively latch the gates of the second set of  $m$  transistors to a high voltage.

16. (Original) The temperature sensor of claim 12, further comprising a trimming circuit connect in parallel to the first variable resistance circuit, wherein the trimming circuit includes a second set of  $m$  transistors connected across the  $m$  resistors of the first variable resistance circuit, respectively, and  $m$  latch circuits which selectively latch the gates of the second set of  $m$  transistors to a high voltage.

17. (Original) The temperature sensor of claim 13, further comprising a trimming circuit connect in parallel to the first variable resistance circuit, wherein the trimming circuit includes a second set of  $m$  transistors connected across the  $m$  resistors of the first variable resistance circuit, respectively, and  $m$  latch circuits which selectively latch the gates of the second set of  $m$  transistors to a high voltage.

18. (Original) The temperature sensor of claim 14, further comprising a trimming circuit connect in parallel to the first variable resistance circuit, wherein the trimming circuit includes a second set of  $m$  transistors connected across the  $m$

resistors of the first variable resistance circuit, respectively, and m latch circuits which selectively latch the gates of the second set of m transistors to a high voltage.

19-33. (Canceled)